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				Application Number			
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				First Named Inventor	Shigeo YOSHII et al.		
				Group Art Unit			
				Examiner Name			
Sheet	1	of	1	Attorney Docket Number	740819-592		
U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS							
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		Office ³	Number ⁴ (if known)				
		Japan	60-167390	Masamichi et al.	08-30-1985		Abstract
		Japan	61-231788	Yoshihiro et al.	10-16-1986		Abstract
		Japan	61-270885	Yoshiro et al.	12-01-1986		Abstract
		Japan	62-189750	Yoshiro et al.	08-19-1987		Abstract
		Japan	62-244186	Mototsugu et al.	10-24-1987		Abstract
		Japan	63-024692	Shuichi	02-02-1988		Abstract
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		J. Shibata et al., "FUNDAMENTAL CHARACTERISTICS OF AN InGaAsP/InP LASER TRANSISTOR", ELECTRONICS LETTERS, Vol. 21, No. 3, pp. 98-100, January 31, 1985.					
		Yoshiro MORI et al., "Operation principle of the InGaAsP/InP laser transistor", Appl. Phys. Lett. 47(7), pp. 649-651, October 1, 1985.					
Examiner Signature	<i>Yoshio Mori</i>	<i>J. MONDT</i>		Date Considered	09/01/2002		

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